

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 62-030330

(43)Date of publication of application : 09.02.1987

(51)Int.Cl.

H01L 21/302
H01L 21/205

(21)Application number : 60-168955

(71)Applicant : TOSHIBA CORP
TOKUDA SEISAKUSHO LTD

(22)Date of filing : 31.07.1985

(72)Inventor : OKANO HARUO
ARIKADO TSUNETOSHI
KANEKO HARUAKI

(54) DRY ETCHING METHOD

(57)Abstract:

PURPOSE: To readily perform a taper etching along a mask irrespective of the rough and dense state of a pattern by using C2F4 as accumulating gas to be added to etching gas.

CONSTITUTION: When C2F4 is used as accumulating gas, a deposition hardly occurs on the periphery of an SiO2 mask, a taper etching is performed along the mask, and the taper etching along the mask is achieved irrespective of the rough and dense state of a pattern. When the C2F4 is used as the accumulating gas, etching gas is not limited to Cl2, but the same result can be obtained even if silicon halogenide, carbon halogenide, phosphorus halogenide, or boron halogenide is used.

LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]